

Product Specifications

PART NO.:

VL495T5669E-E7S/E6S/D5S

REV: 1.1

General Information

2GB 256Mx72 DDR2 SDRAM VLP ECC REGISTERED Mini-RDIMM 244-PIN

Description

The VL495T5669E is a 256Mx72 DDR2 SDRAM high density Mini-RDIMM. This memory module is dual rank, consists of nine stacked CMOS 256Mx8 bit with 8 banks DDR2 synchronous DRAMs in BGA packages, two 25-bit registered buffers in BGA package, a zero delay PLL clock in BGA package, and a 2K EEPROM in an 8-pin MLF package. This module is a 244-pin mini dual in-line memory module and is intended for mounting into an edge connector socket. Decoupling capacitors are mounted on the printed circuit board for each DDR2 SDRAM.

Features

- 244-pin, registered mini dual in-line memory module (Mini-RDIMM)
- JEDEC pin out
- Supports ECC error detection and correction
- Fast data transfer rates: PC2-6400, PC2-5300, PC2-4200
- VDD = VDDQ = 1.8V
- JEDEC standard 1.8V (SSTL_18 compatible)
- VDDSPD = 1.7V to 3.6V
- Differential data strobe (DQS, DQS#) option
- Differential clock inputs (CK, CK#)
- Four-bit pre-fetch architecture
- DLL aligns DQ and DQS transition with CK
- Nominal and dynamic on-die termination (ODT)
- Programmable CAS# latency: 6 (DDR2-800), 5 (DDR2-667), 4 (DDR2-533)
- Write latency = Read latency - 1 tCK
- Eight internal component banks for concurrent operation
- Programmable burst; length (4, 8)
- Adjustable data-output drive strength
- Auto & self refresh, (8K/64ms refresh)
- Serial presence detect (SPD) with EEPROM
- Gold edge contacts
- Lead-free, RoHS compliant
- PCB: Height 18.29mm (0.720"), double sided components

Pin Description

Pin Name	Function
A0~A13	Address Inputs
A10/AP	Address Input/ Autoprecharge
BA0~BA2	Bank Address Inputs
DQ0~DQ63	Data Input/Output
DQS0~DQS8	Data Strobes
DQS0#~DQS8#	Data Strobes Complement
CB0~CB7	Check Bits
DM0~DM8	Data Masks
CK0, CK0#	Clock Input
ODT0, ODT1	On-die Termination Control
CKE0, CKE1	Clock Enables
CS0#, CS1#	Chip Selects
RAS#	Row Address Strobes
CAS#	Column Address Strobes
WE#	Write Enable
VDD	Voltage Supply 1.8V +/- 0.1V
VSS	Ground
SA0~SA2	SPD Address
SDA	SPD Data Input/Output
SCL	SPD Clock Input
VDDSPD	SPD Voltage Supply 1.7V to 3.6V
VREF	SSTL_18 Reference Voltage
NC	No Connect

Order Information:

VL495T5669E - E7 S X

DRAM DIE (Option)

DRAM MANUFACTURER
S - SAMSUNG

MODULE SPEED
E7: PC2-6400 @ CL6
E6: PC2-5300 @ CL5
D5: PC2-4200 @ CL4

VL: Lead-free/RoHS

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Pin Configuration

244-PIN DDR2 Mini-RDIMM FRONT SIDE

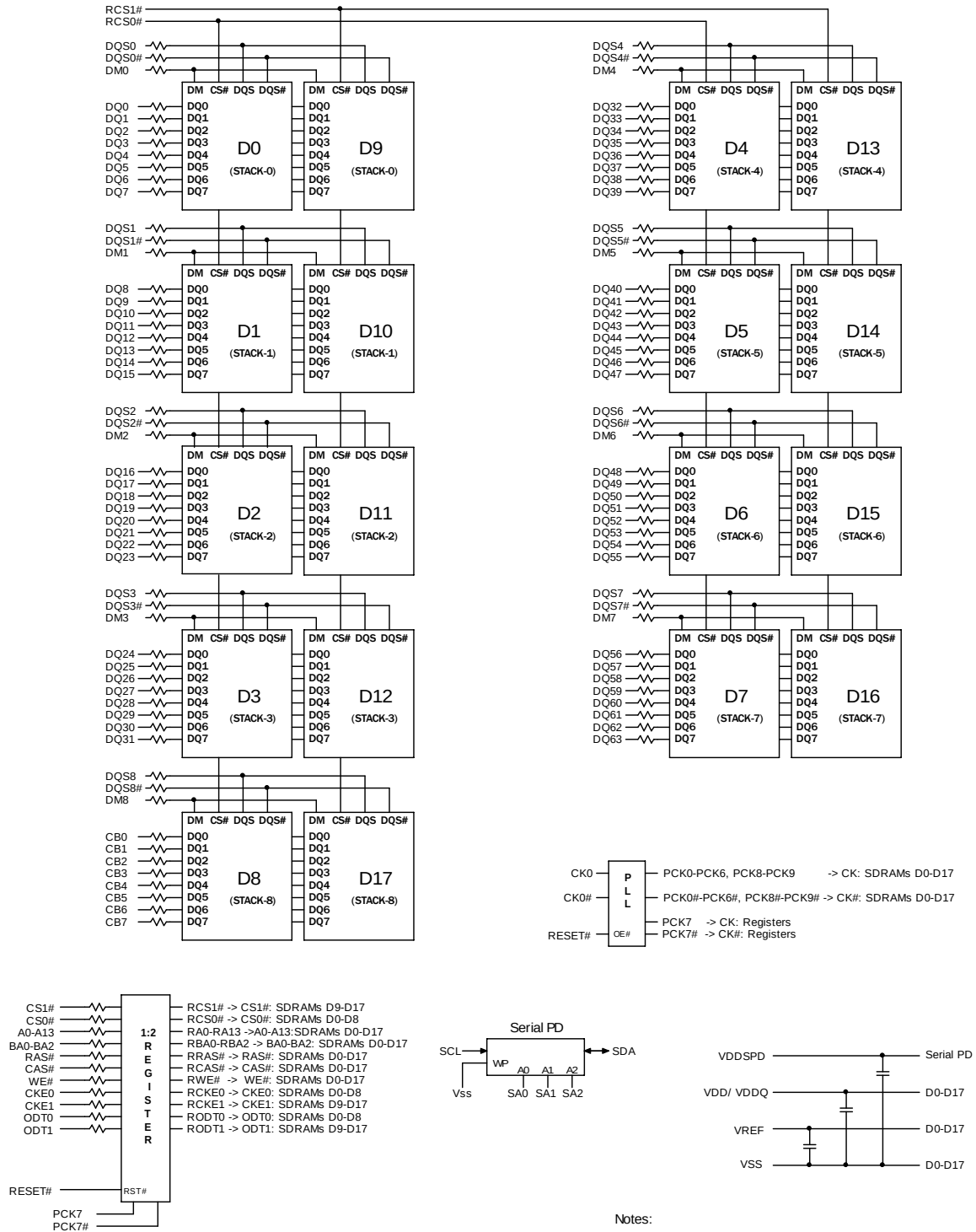
Pin	Name	Pin	Name	Pin	Name	Pin	Name
1	VREF	32	VSS	63	VDDQ	93	VSS
2	VSS	33	DQ24	64	A2	94	DQS5#
3	DQ0	34	DQ25	65	VDD	95	DQS5
4	DQ1	35	VSS	KEY		96	VSS
5	VSS	36	DQS3#	66	VSS	97	DQ42
6	DQS0#	37	DQS3	67	VSS	98	DQ43
7	DQS0	38	VSS	68	NC	99	VSS
8	VSS	39	DQ26	69	VDD	100	DQ48
9	DQ2	40	DQ27	70	A10/ AP	101	DQ49
10	DQ3	41	VSS	71	BA0	102	VSS
11	VSS	42	CB0	72	VDD	103	SA2
12	DQ8	43	CB1	73	WE#	104	NC
13	DQ9	44	VSS	74	VDDQ	105	VSS
14	VSS	45	DQS8#	75	CAS#	106	DQS6#
15	DQS1#	46	DQS8	76	VDDQ	107	DQS6
16	DQS1	47	VSS	77	CS1#	108	VSS
17	VSS	48	CB2	78	OTD1	109	DQ50
18	RESET#	49	CB3	79	VDDQ	110	DQ51
19	NC	50	VSS	80	NC	111	VSS
20	VSS	51	NC	81	VSS	112	DQ56
21	DQ10	52	VDDQ	82	DQ32	113	DQ57
22	DQ11	53	CKE0	83	DQ33	114	VSS
23	VSS	54	VDD	84	VSS	115	DQS7#
24	DQ16	55	BA2	85	DQS4#	116	DQS7
25	DQ17	56	NC	86	DQS4	117	VSS
26	VSS	57	VDDQ	87	VSS	118	DQ58
27	DQS2#	58	A11	88	DQ34	119	DQ59
28	DQS2	59	A7	89	DQ35	120	VSS
29	VSS	60	VDD	90	VSS	121	SA0
30	DQ18	61	A5	91	DQ40	122	SA1
31	DQ19	62	A4	92	DQ41		

244-PIN DDR2 Mini-RDIMM BACK SIDE

Pin	Name	Pin	Name	Pin	Name	Pin	Name
123	VSS	154	DQ28	185	A3	215	DM5
124	DQ4	155	DQ29	186	A1	216	NC
125	DQ5	156	VSS	187	VDD	217	VSS
126	VSS	157	DM3	KEY		218	DQ46
127	DM0	158	NC	188	CK0	219	DQ47
128	NC	159	VSS	189	CK0#	220	VSS
129	VSS	160	DQ30	190	VDD	221	DQ52
130	DQ6	161	DQ31	191	A0	222	DQ53
131	DQ7	162	VSS	192	BA1	223	VSS
132	VSS	163	CB4	193	VDD	224	NC
133	DQ12	164	CB5	194	RAS#	225	NC
134	DQ13	165	VSS	195	VDDQ	226	VSS
135	VSS	166	DM8	196	CS0#	227	DM6
136	DM1	167	NC	197	VDDQ	228	NC
137	NC	168	VSS	198	ODT0	229	VSS
138	VSS	169	CB6	199	A13	230	DQ54
139	NC	170	CB7	200	VDD	231	DQ55
140	NC	171	VSS	201	NC	232	VSS
141	VSS	172	NC	202	VSS	233	DQ60
142	DQ14	173	VDDQ	203	DQ36	234	DQ61
143	DQ15	174	CKE1	204	DQ37	235	VSS
144	VSS	175	VDD	205	VSS	236	DM7
145	DQ20	176	A15 *	206	DM4	237	NC
146	DQ21	177	A14 *	207	NC	238	VSS
147	VSS	178	VDDQ	208	VSS	239	DQ62
148	DM2	179	A12	209	DQ38	240	DQ63
149	NC	180	A9	210	DQ39	241	VSS
150	VSS	181	VDD	211	VSS	242	SDA
151	DQ22	182	A8	212	DQ44	243	SCL
152	DQ23	183	A6	213	DQ45	244	VDDSPD
153	VSS	184	VDDQ	214	VSS		

*: These pins are not used in this module.
 RESET# (Pin 18) is connected to both OE of the PLL and RESET# of the register

Function Block Diagram



Notes:

1. Unless otherwise noted, resistor values are 22 ohms +/-5%

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Absolute Maximum Ratings

Absolute Maximum Ratings					
Symbol	Parameter		MIN	MAX	Unit
VDD	Voltage on VDD pin relative to VSS		-1.0	2.3	V
VDDQ	Voltage on VDDQ pin relative to VSS		-0.5	2.3	V
VDDL	Voltage on VDDL pin relative to VSS		-0.5	2.3	V
VIN, VOUT	Voltage on any pin relative to VSS		-0.5	2.3	V
TSTG	Storage temperature		-55	100	°C
IL	Input leakage current; Any input 0V<VIN<VDD; VREF input 0V<VIN<0.95V; Other pins not under test = 0V	Address, BA, RAS#, CAS#, WE#	-5	5	uA
		CS#, CKE, ODT	-5	5	uA
		CK, CK#	-250	+250	uA
		DM	-10	10	uA
IOZ	Output leakage current; 0V<VOUT<VDDQ; DQs and ODT are disabled	DQ, DQS, DQS#	-10	10	uA
IVREF	VREF supply leakage current; VREF = Valid VREF level		-36	36	uA

DC Operating Conditions

Symbol	Parameter	Min	Typical	Max	Unit	Notes
VDD	Supply voltage	1.7	1.8	1.9	V	1
VDDQ	I/O supply voltage	1.7	1.8	1.9	V	4
VDDL	VDDL supply voltage	1.7	1.8	1.9	V	4
VREF	I/O reference voltage	0.49 x VDDQ	0.50 x VDDQ	0.51 x VDDQ	V	2
VTT	I/O termination voltage	VREF-0.04	VREF	VREF+0.04	V	3

Note:

- VDD, VDDQ must track each other. VDDQ must be less than or equal to VDD.
- VREF is expected to equal VDDQ/2 of the transmitting device and to track variations in the DC level of the same. Peak-to-peak noise on VREF may not exceed +/-1percent of the DC value. Peak-to-peak AC noise on VREF may not exceed +/-2 percent of VREF. This measurement is to be taken at the nearest VREF bypass capacitor.
- VTT is not applied directly to the device. VTT is a system supply for signal termination resistors, is expected to be set equal to VREF and must track variations in the DC level of VREF.
- VDDQ tracks with VDD; VDDL tracks with VDD.

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Operating Temperature Condition

Symbol	Parameter	Rating	Units	Notes
TOPER	Operating temperature	0 - 95	°C	1,2
Notes: 1. Operating temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JEDEC JESD51-2. 2. At 0 – 85°C, operation temperature range, all DRAM specifications will be supported. The refresh rate is required to double when 85°C < TOPER ≤ 95°C.				

Input DC Logic Level

All voltages referenced to VSS

Symbol	Parameter	Min	Max	Unit
VIH(DC)	Input High (Logic 1) Voltage	VREF + 0.125	VDDQ + 0.300	V
VIL(DC)	Input Low (Logic 0) Voltage	-0.300	VREF - 0.125	V

Input AC Logic Level

All voltages referenced to VSS

Symbol	Parameter	Min	Max	Unit
VIH(AC)	Input High (Logic 1) Voltage DDR2-533	VREF + 0.250	-	V
VIH(AC)	Input High (Logic 1) Voltage DDR2-800, DDR2-667	VREF + 0.200	-	V
VIL(AC)	Input Low (Logic 0) Voltage DDR2-533	-	VREF - 0.250	V
VIL(AC)	Input Low (Logic 0) Voltage DDR2-800, DDR2-667	-	VREF - 0.200	V

Input/Output Capacitance

TA=25°C, f=100MHz

Parameter	Symbol	E7/E6 (DDR2-800/677)		D5 (DDR2-533)		Unit
		Min	Max	Min	Max	
Input capacitance (A0~A13, BA0~BA2, RAS#, CAS#, WE#)	CIN1	6.5	7.5	6.5	7.5	pF
Input capacitance (CKE0, CKE1), (ODT0, ODT1), (CS0#, CS1#)	CIN2	6.5	7.5	6.5	7.5	pF
Input capacitance (CK0, CK0#)	CIN3	6	7	6	7	pF
Input/Output capacitance (DQ, DQS, DQS#, DM, CB)	CIO	9	11	9	12	pF

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IDD Specification

Condition	Symbol	E7 (DDR2-800)	E6 ⁽²⁾ (DDR2-667)	D5 ⁽²⁾ (DDR2-533)	Unit	
Operating one bank active-pre-charge; t _{CK} = t _{CK(IDD)} ; t _{RC} = t _{RC(IDD)} ; t _{RAS} = t _{RAS MIN(IDD)} ; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING	IDD0*	895	877	877	mA	
Operating one bank active-read-pre-charge; IOUT = 0mA; BL = 4; CL = CL(IDD); AL = 0; t _{CK} = t _{CK(IDD)} ; t _{RC} = t _{RC(IDD)} ; t _{RAS} = t _{RAS MIN(IDD)} ; t _{RCD} = t _{RCD(IDD)} ; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as IDD4W.	IDD1*	949	922	922	mA	
Pre-charge power-down current; All banks idle; t _{CK} = t _{CK(IDD)} ; CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	IDD2P**	580	580	580	mA	
Pre-charge quiet standby current; All banks idle; t _{CK} = t _{CK(IDD)} ; CKE is HIGH; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	IDD2Q**	760	760	760	mA	
Pre-charge standby current; All banks idle; t _{CK} = t _{CK(IDD)} ; CKE is HIGH; Other control and address bus inputs are STABLE; Data bus inputs are SWITCHING.	IDD2N**	850	832	832	mA	
Active power-down current; All banks open; t _{CK} = t _{CK(IDD)} ; CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING.	Fast PDN Exit MRS(12) = 0 Slow PDN Exit MRS(12) = 1	IDD3P**	814	796	796	mA
		670	670	670	mA	
Active standby current; All banks open; t _{CK} = t _{CK(IDD)} ; t _{RP} = t _{RP(IDD)} ; t _{RAS} = t _{RAS MAX(IDD)} ; CKE is HIGH, CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING.	IDD3N**	976	940	940	mA	
Operating burst write current; All banks open; Continuous burst writes; BL = 8; CL = CL(IDD); AL = 0; t _{CK} = t _{CK(IDD)} ; t _{RAS} = t _{RAS MAX(IDD)} ; t _{RP} = t _{RP(IDD)} ; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING	IDD4W*	1093	1030	1030	mA	
Operating burst read current; All banks open; Continuous burst reads; IOUT = 0mA; BL = 4; CL = CL(IDD); AL = 0; t _{CK} = t _{CK(IDD)} ; t _{RAS} = t _{RAS MAX(IDD)} ; t _{RP} = t _{RP(IDD)} ; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as IDD4W.	IDD4R*	1210	1120	1120	mA	
Burst refresh current; t _{CK} =t _{CK(IDD)} ; Refresh command at every t _{RFC(IDD)} interval; CKE is HIGH; CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING.	IDD5**	2290	2200	2200	mA	
Self refresh current; CK and CK# at 0V; CKE < 0.2V; Other control and address bus inputs are FLOATING; Data bus inputs are FLOATING.	Normal	IDD6**	180	180	180	mA
Operating bank interleave read current; All bank interleaving reads; IOUT = 0mA; BL = 8; CL = CL(IDD); AL = t _{RCD(IDD)} - 1*t _{CK(IDD)} ; t _{CK} = t _{CK(IDD)} ; t _{RC} = t _{RC(IDD)} ; t _{RRD} = t _{RRD(IDD)} ; t _{RCD} = 1*t _{CK(IDD)} ; CKE is HIGH; CS# is HIGH between valid commands; Address bus inputs are STABLE during DESELECTs; Data bus inputs are SWITCHING.	IDD7*	1930	1795	1795	mA	

Notes: 1. IDD specification is based on Samsung F-die components.

2. The DRAM's speed DDR2-667 can support speed DDR2-533.

*: Value calculated as one module rank in this operating condition, and all other module ranks in IDD2P (CKE LOW) mode.

**.: Value calculated reflects all module ranks in this operating condition.

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AC TIMING PARAMETERS & SPECIFICATIONS

Parameter		Symbol	E7 (DDR2-800)		E6 (DDR2-667)		D5 (DDR2-533)		Unit
			Min	Max	Min	Min	Max	Min	
Clock Timing									
Clock Cycle Time	CL6	t _{CK} (6)	2500	8000	-	-	-	-	ps
	CL5	t _{CK} (5)	3000	8000	3000	8000	-	-	ps
	CL4	t _{CK} (4)	3750	8000	3750	8000	3750	8000	ps
CK high-level width		t _{CH} (avg)	0.48	0.52	0.48	0.52	0.48	0.52	t _{CK}
CK low-level width		t _{CL} (avg)	0.48	0.52	0.48	0.52	0.48	0.52	t _{CK}
Half clock period		t _{HP}	MIN (t _{CH} , t _{CL})	-	MIN (t _{CH} , t _{CL})	-	MIN (t _{CH} , t _{CL})	-	ps
Clock jitter		t _{JIT}	-100	100	-125	125	-125	125	ps
Data Timing									
DQ output access time from CK/CK#		t _{AC}	-400	400	-450	+450	-500	500	ps
Data-out high impedance window from CK/CK#		t _{HZ}	-	t _{AC} (MAX)	-	t _{AC} (MAX)	-	t _{AC} (MAX)	ps
Data-out low impedance window from CK/CK#		t _{LZ}	t _{AC} (MIN)	t _{AC} (MAX)	t _{AC} (MIN)	t _{AC} (MAX)	t _{AC} (MIN)	t _{AC} (MAX)	ps
DQ and DM input setup time relative to DQS		t _{DS}	50	-	100	-	100	-	ps
DQ and DM input hold time relative to DQS		t _{DH}	125	-	175	-	225	-	ps
DQ and DM input pulse width (for each input)		t _{DIPW}	0.35	-	0.35	-	0.35	-	t _{CK}
Data hold skew factor		t _{QHS}	-	300	-	340	-	400	ps
DQ-DQS hold, DQS to first DQ to go non-valid, per access		t _{QH}	t _{HP} - t _{QHS}	-	t _{HP} - t _{QHS}	-	t _{HP} - t _{QHS}	-	ps
Data valid output window (DVW)		t _{DVW}	t _{QH} -t _{DQSQ}	-	t _{QH} -t _{DQSQ}	-	t _{QH} -t _{DQSQ}	-	ns
Data Strobe Timing									
DQS input high pulse width		t _{DQSH}	0.35	-	0.35	-	0.35	-	t _{CK}
DQS input low pulse width		t _{DQSL}	0.35	-	0.35	-	0.35	-	t _{CK}
DQS output access time from CK/CK#		t _{DQSCK}	-350	+350	-400	+400	-450	+450	ps
DQS failing edge to CK rising-setup time		t _{DSS}	0.2	-	0.2	-	0.2	-	t _{CK}
DQS failing edge from CK rising-hold time		t _{DSH}	0.2	-	0.2	-	0.2	-	t _{CK}
DQS-DQ skew, DQS to last DQ valid, per group, per access		t _{DQSQ}	-	200	-	240	-	300	ps
DQS read preamble		t _{RPRE}	0.9	1.1	0.9	1.1	0.9	1.1	t _{CK}
DQS read preamble		t _{RPST}	0.4	0.6	0.4	0.6	0.4	0.6	t _{CK}
DQS read preamble setup time		t _{WPRES}	0	-	0	-	0	-	ps
DQS read preamble		t _{WPRE}	0.35	-	0.35	-	0.25	-	t _{CK}
DQS read preamble		t _{WPST}	0.4	0.6	0.4	0.6	0.4	0.6	t _{CK}
Write command to first DQS latching transition		t _{DQSS}	WL-0.25	WL+0.25	WL-0.25	WL+0.25	WL-0.25	WL+0.25	t _{CK}

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AC TIMING PARAMETERS & SPECIFICATIONS

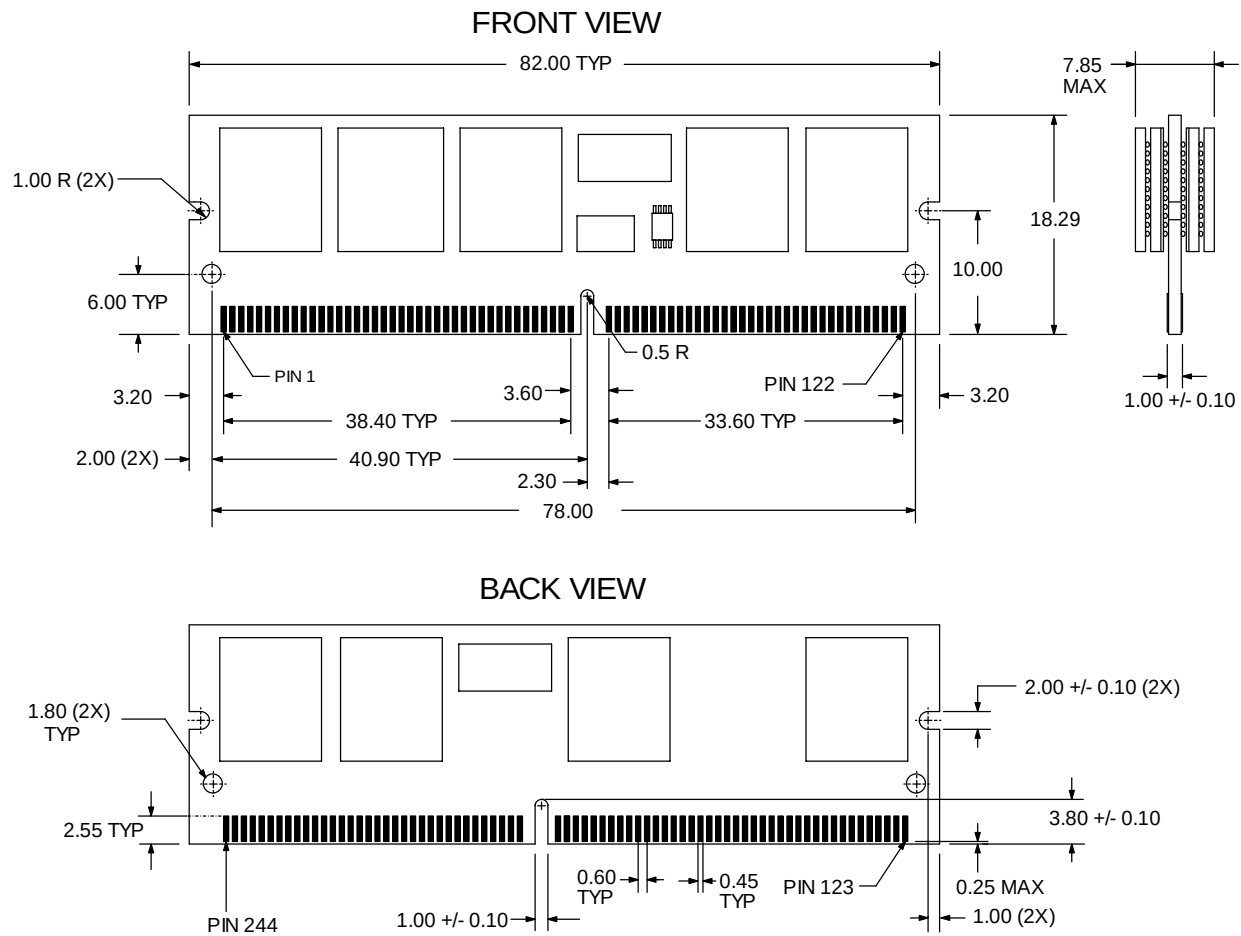
Parameter	Symbol	E7 (DDR2-800)		E6 (DDR2-667)		D5 (DDR2-533)		Unit
		Min	Max	Min	Max	Min	Max	
Command and Address Timing								
Address and control input pulse width for each input	t _{IPW}	0.6	-	0.6	-	0.6	-	t _{CK}
Address and control input setup time	t _{IS}	175	-	200	-	250	-	ps
Address and control input hold time	t _{IH}	250	-	275	-	375	-	ps
CAS# to CAS# command delay	t _{CCD}	2	-	2	-	2	-	t _{CK}
ACTIVE to ACTIVE (same bank) command	t _{RC}	60	-	60	-	60	-	ns
ACTIVE bank a to ACTIVE bank b command	t _{RRD}	7.5	-	7.5	-	7.5	-	ns
ACTIVE to READ or WRITE delay	t _{RCD}	15	-	15	-	15	-	ns
Four Bank Activate period	t _{FAW}	37.5	-	37.5	-	37.5	-	ns
ACTIVE to PRECHARGE command	t _{RAS}	45	70,000	45	70,000	45	70,000	ns
Internal READ to precharge Command delay	t _{RTP}	7.5	-	7.5	-	7.5	-	ns
Write recovery time	t _{WR}	15	-	15	-	15	-	ns
Auto precharge write recovery + precharge time	t _{DAL}	t _{WR} +t _{RP}	-	t _{WR} +t _{RP}	-	t _{WR} +t _{RP}	-	t _{CK}
Internal WRITE to READ Command delay	t _{WTR}	7.5	-	7.5	-	7.5	-	ns
PRECHARGE command period	t _{RP}	15	-	15	-	15	-	ns
PRECHARGE ALL command period	t _{RPA}	t _{RP} +t _{CK}	-	t _{RP} +t _{CK}	-	t _{RP} +t _{CK}	-	ns
LOAD MODE command cycle time	t _{MRD}	2	-	2	-	2	-	t _{CK}
CKE low to CK, CK# uncertainty	t _{DELAY}	t _{IS} +t _{CK} +t _{IH}	-	t _{IS} +t _{CK} +t _{IH}	-	t _{IS} +t _{CK} +t _{IH}	-	ns
Self Refresh								
Refresh to Active or Refresh to Refresh command interval	t _{RFC}	127.5	-	127.5	-	127.5	-	ns
Average periodic Refresh interval	t _{REFI}	-	7.8	-	7.8	-	7.8	us
Exit Self Refresh to non-READ command	t _{XSNR}	t _{RFC(MIN)} +10	-	t _{RFC(MIN)} +10	-	t _{RFC(MIN)} +10	-	ns
Exit Self Refresh to READ	t _{XSRD}	200	-	200	-	200	-	t _{CK}
Exit Self Refresh timing reference	t _{ISXR}	t _{IS}	-	t _{IS}	-	t _{IS}	-	ps
ODT								
ODT turn-on delay	t _{AOND}	2	2	2	2	2	2	t _{CK}
ODT turn-on	t _{AON}	t _{AC(MIN)}	t _{AC(MAX)} +600	t _{AC(MIN)}	t _{AC(MAX)} +700	t _{AC(MIN)}	t _{AC(MAX)} +1000	ps
ODT turn-off delay	t _{AOFD}	2.5	2.5	2.5	2.5	2.5	2.5	t _{CK}
ODT turn-off	t _{AOF}	t _{AC(MIN)}	t _{AC(MAX)} +600	t _{AC(MIN)}	t _{AC(MAX)} +600	t _{AC(MIN)}	t _{AC(MAX)} +600	ps
ODT turn-on(power-down mode)	t _{AONPD}	t _{AC(MIN)} +2000	2 x t _{CK} + t _{AC(MAX)} +1000	t _{AC(MIN)} +2000	2 x t _{CK} + t _{AC(MAX)} +1000	t _{AC(MIN)} +2000	2 x t _{CK} + t _{AC(MAX)} +1000	ps
ODT turn-off (power-down mode)	t _{AOFPD}	t _{AC(MIN)} +2000	2.5 x t _{CK} + t _{AC(MAX)} +1000	t _{AC(MIN)} +2000	2.5 x t _{CK} + t _{AC(MAX)} +1000	t _{AC(MIN)} +2000	2.5 x t _{CK} + t _{AC(MAX)} +1000	ps
ODT to power-down entry latency	t _{ANPD}	3	-	3	-	3	-	t _{CK}
ODT power-down exit latency	t _{AXPD}	8	-	8	-	8	-	t _{CK}
Power Down								
Exit active power-down to READ command, MR[bit12=0]	t _{XARD}	2	-	2	-	2	-	t _{CK}
Exit active power-down to READ command, MR[bit12=1]	t _{XARDS}	8-AL	-	7-AL	-	6-AL	-	t _{CK}
Exit precharge power-down to any non-READ command	t _{XP}	2	-	2	-	2	-	t _{CK}
CKE minimum high/low time	t _{CKE}	3	-	3	-	3	-	t _{CK}

Product Specifications

PART NO.:

VL495T5669E-E7S/E6S/D5S
REV: 1.1

Package Dimensions



Note: 1. All dimensions are in millimeters with tolerance $\pm 0.15\text{mm}$ unless otherwise specified.
 2. The dimensional diagram is for reference only.

Product Specifications		
PART NO.:	VL495T5669E-E7S/E6S/D5S	REV: 1.1

Revision History:

Date	Rev.	Page	Changes
10/28/2010	1.0	All	Spec release
12/22/2010	1.1	1	Update General Information